

# **isc Silicon NPN Power Transistor**

### **DESCRIPTION**

- · High Breakdown Voltage-
  - : V<sub>(BR)CBO</sub>= 1500V(Min)
- · High Switching Speed
- High Reliability
- Built-in Damper Diode
- · Minimum Lot-to-Lot variations for robust device performance and reliable operation

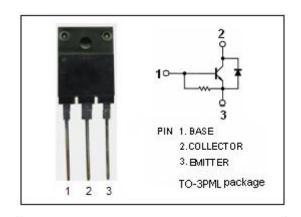


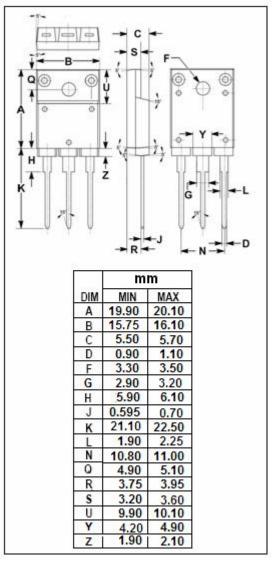
## **APPLICATIONS**

 Ultrahigh-definition CRT display horizontal deflection output applications

ABSOLUTE MAXIMUM RATINGS(Ta=25℃)

SYMBOL	PARAMETER	VALUE	UNIT	
V <sub>CBO</sub>	Collector-Base Voltage	1500	V	
Vceo	Collector-Emitter Voltage	800	V	
V <sub>EBO</sub>	Emitter-Base Voltage	6	V	
Ic	Collector Current-Continuous	8	А	
I <sub>CP</sub>	Collector Current-Peak	25	А	
Pc	Collector Power Dissipation @ T <sub>a</sub> =25℃	3.0	W	
	Collector Power Dissipation @ T <sub>C</sub> =25°C	70		
TJ	Junction Temperature	150	$^{\circ}$ C	
T <sub>stg</sub>	Storage Temperature Range	-55~150	$^{\circ}$	







# isc Silicon NPN Power Transistor

2SC4124

### **ELECTRICAL CHARACTERISTICS**

Tc=25℃ unless otherwise specified

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SYMBOL	PARAMETER	CONDITIONS	MIN	TYP.	MAX	UNIT			
V <sub>CEO(SUS)</sub>	Collector-Emitter Sustaining Voltage	I <sub>C</sub> = 10mA; I <sub>B</sub> = 0	800			V			
V <sub>CE(sat)</sub>	Collector-Emitter Saturation Voltage	I <sub>C</sub> = 6A; I <sub>B</sub> = 1.5A			5.0	V			
V <sub>BE(sat)</sub>	Base-Emitter Saturation Voltage	I <sub>C</sub> = 6A; I <sub>B</sub> = 1.5A			1.5	V			
I <sub>CBO</sub>	Collector Cutoff Current	V <sub>CB</sub> = 800V; I <sub>E</sub> = 0			10	μА			
Ices	Collector Cutoff Current	V <sub>CE</sub> = 1500V; R <sub>BE</sub> = 0			1.0	mA			
I <sub>EBO</sub>	Emitter Cutoff Current	V <sub>EB</sub> = 4V; I <sub>C</sub> = 0	40		130	mA			
h <sub>FE-1</sub>	DC current gain	I <sub>C</sub> = 1A; V <sub>CE</sub> = 5V	8						
h <sub>FE-2</sub>	DC current gain	Ic= 6A; V <sub>CE</sub> = 5V	4		6				
Switching times									
t <sub>stg</sub>	Storage Time	Ic= 6A, I <sub>B1</sub> = 1.2A; I <sub>B2</sub> = -2.4A			3.0	μS			
t <sub>f</sub>	Fall Time	R <sub>L</sub> = 33.3 $\Omega$ ; V <sub>CC</sub> = 200V			0.2	μs			

### **NOTICE:**

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